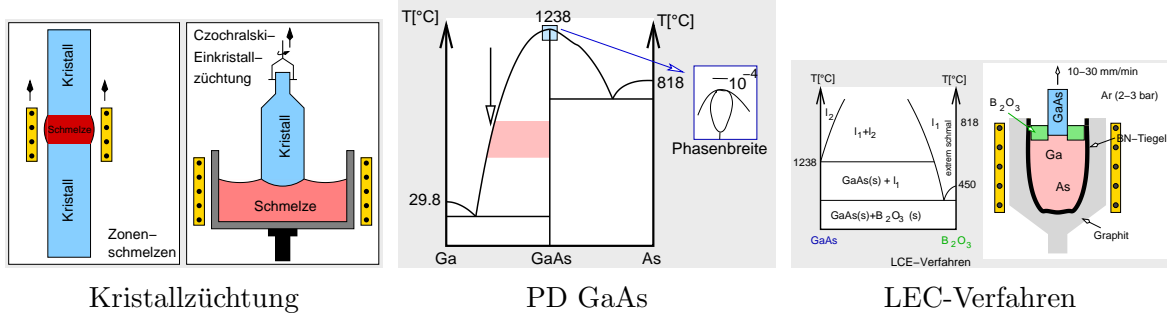


3. Herstellung von Halbleitern

3.1. Substratherstellung

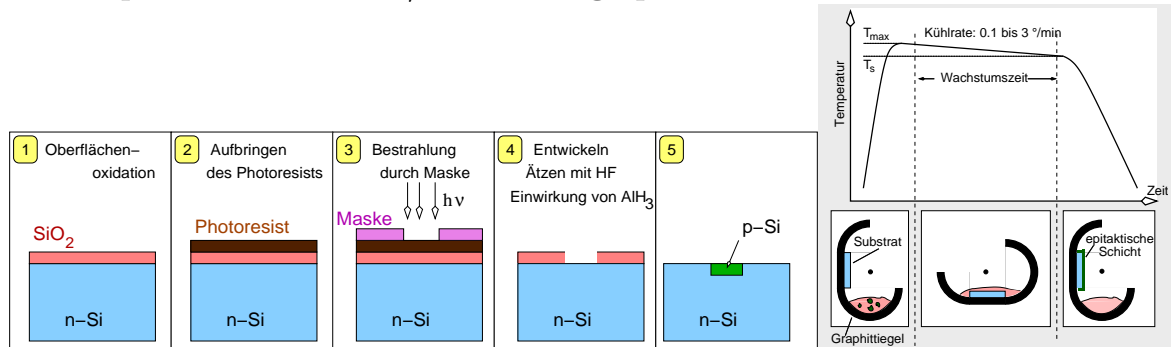


Kristallzüchtung

PD GaAs

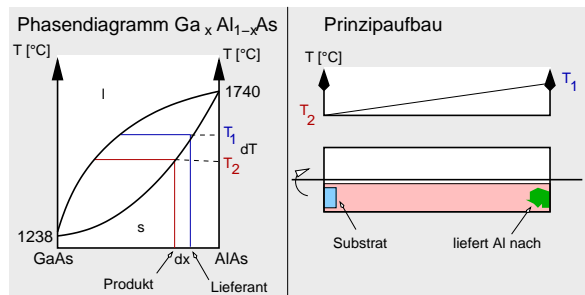
LEC-Verfahren

3.2. Depositionsverfahren/Herstellung epitaktischer Materialien

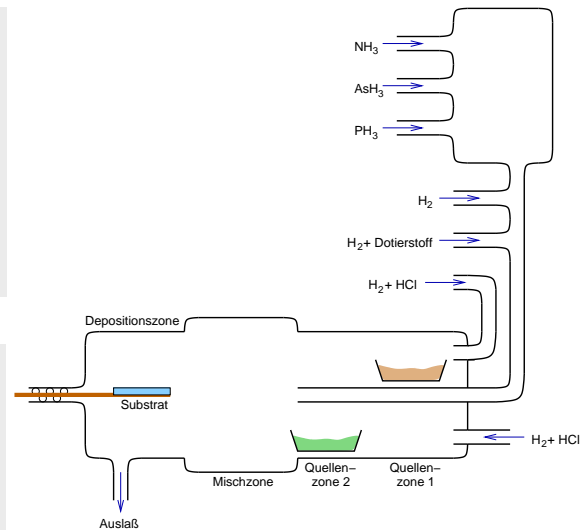
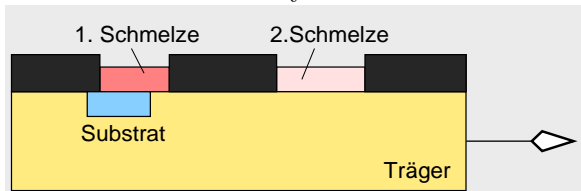


Diffusionsverfahren

LPE II: Tipping

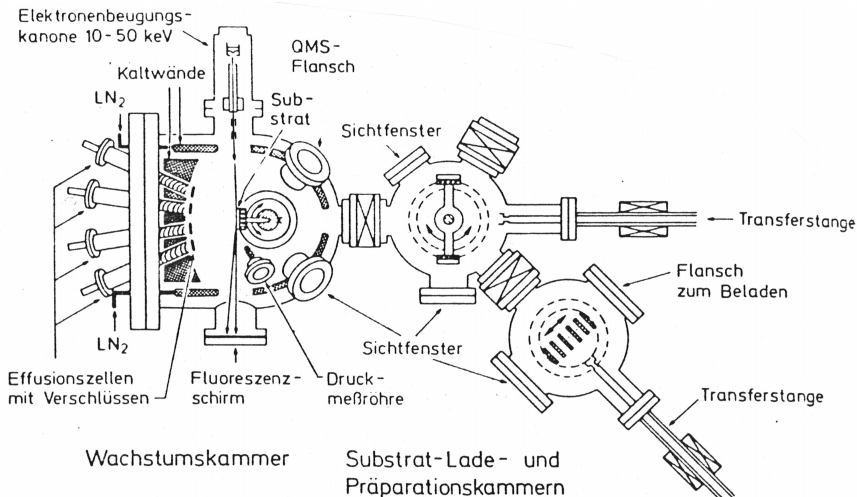


LPE III: Steady-State-Technik



Chemical Vapor Deposition (CVD)

LPE IV: Sliding



Molekularstrahl-Epitaxie (MBE)